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List of articles citing

Large-grain MBE-grown GaSe on GaAs with a Mexican hat-like valence band dispersion

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#	Paper	IF	Citations
39	Electronic Properties of Transferable Atomically Thin MoSe ₂ /h-BN Heterostructures Grown on Rh(111). <i>ACS Nano</i> , 2018 , 12, 11161-11168	16.7	14
38	Multiple Optical Frequency Conversions in Few-Layer GaSe Assisted by a Photonic Crystal Cavity. <i>Advanced Optical Materials</i> , 2018 , 6, 1800698	8.1	14
37	Epitaxial growth of InSe and In ₂ Se ₃ and In ₂ Se ₃ on GaSe. <i>2D Materials</i> , 2018 , 5, 035026	5.9	55
36	Selective Growth of Two-Dimensional Heterostructures of Gallium Selenide on Monolayer Graphene and the Thickness Dependent p- and n-Type Nature. <i>ACS Applied Nano Materials</i> , 2018 , 1, 3293-3302	5.6	4
35	Structural, vibrational, and electronic properties of single-layer hexagonal crystals of group IV and V elements. <i>Physical Review B</i> , 2018 , 98,	3.3	53
34	A Perspective on the Application of Spatially Resolved ARPES for 2D Materials. <i>Nanomaterials</i> , 2018 , 8,	5.4	27
33	Synthesis, Characterization, and Properties of Graphene Analogs of 2D Material. 2019 , 91-143		7
32	Group IIIA/IVA monochalcogenides nanosheets for ultrafast photonics. <i>APL Photonics</i> , 2019 , 4, 090801	5.2	12
31	Indirect to Direct Gap Crossover in Two-Dimensional InSe Revealed by Angle-Resolved Photoemission Spectroscopy. <i>ACS Nano</i> , 2019 , 13, 2136-2142	16.7	40
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27	Screw-Dislocation-Driven Growth Mode in Two Dimensional GaSe on GaAs(001) Substrates Grown by Molecular Beam Epitaxy. <i>Scientific Reports</i> , 2019 , 9, 17781	4.9	10
26	Stability, spontaneous and induced polarization in monolayer MoC, WC, WS, and WSe. <i>Journal of Physics Condensed Matter</i> , 2019 , 31, 045301	1.8	3
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22	Polytypism in few-layer gallium selenide. <i>Nanoscale</i> , 2020 , 12, 8563-8573	7.7	11
21	Thermoelectric properties of Mexican-hat band structures. <i>Advances in Natural Sciences: Nanoscience and Nanotechnology</i> , 2020 , 11, 015012	1.6	3
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17	Ballistic thermoelectric transport properties of two-dimensional group III-VI monolayers. <i>Physical Review B</i> , 2021 , 103,	3.3	2
16	Bottom-Up Engineering Strategies for High-Performance Thermoelectric Materials. <i>Nano-Micro Letters</i> , 2021 , 13, 119	19.5	15
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- 2 Lab-on-Fiber Based on Optimized Gallium Selenide for Femtosecond Mode-Locked Lasers and Fiber-Compatible Photodetectors. **2023**, 4,
- 1 Two-dimensional single crystal monoclinic gallium telluride on silicon substrate via transformation of epitaxial hexagonal phase. **2023**, 7,